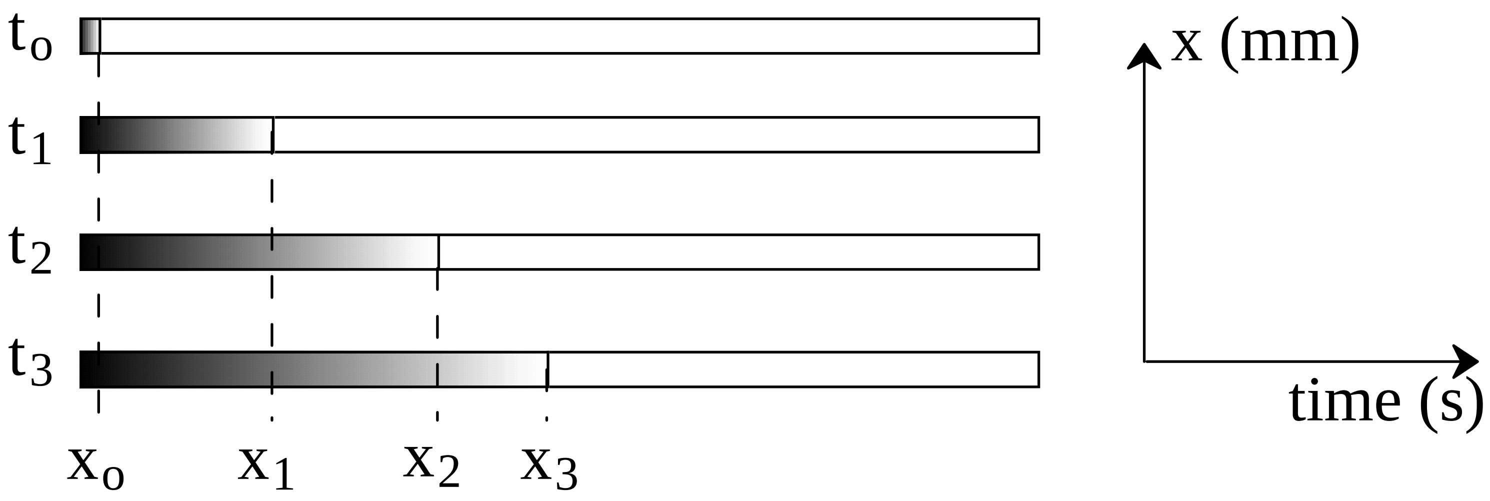
CHAPTER 5:
Diffusion in solids

ISSUES TO ADDRESS...

- How does diffusion occur?
- Why is it an important part of processing?
- How can the rate of diffusion be predicted for some simple cases?
- How does diffusion depend on structure and temperature?

Diffusion demo

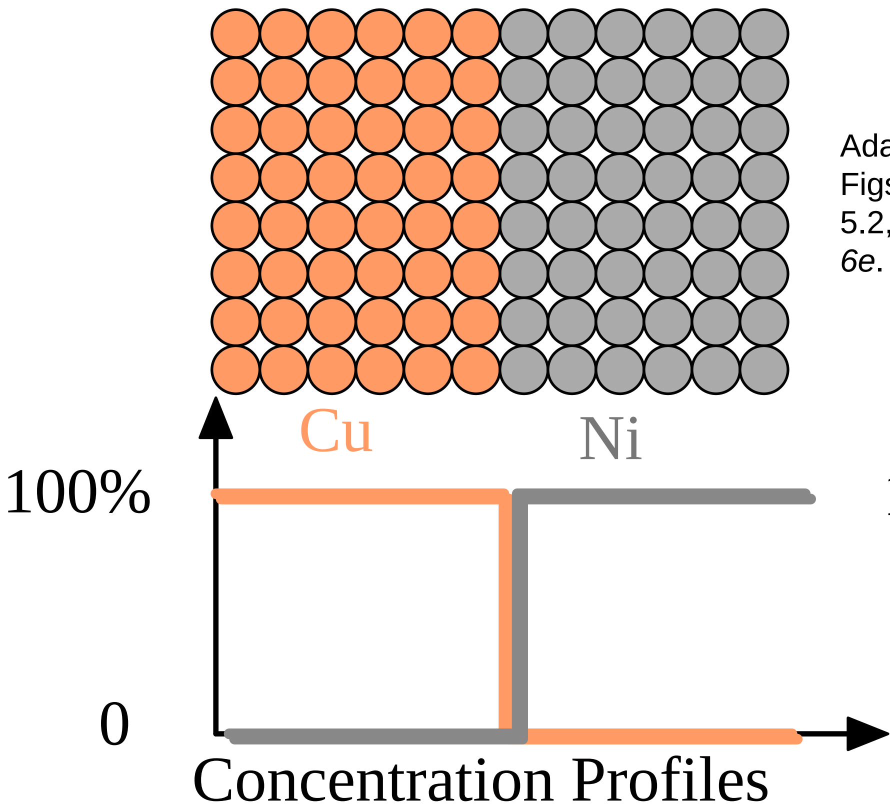
- Glass tube filled with water.
- At time t = 0, add some drops of ink to one end of the tube.
- Measure the diffusion distance, x, over some time.
- Compare the results with theory.



Diffusion: the phenomena (1)

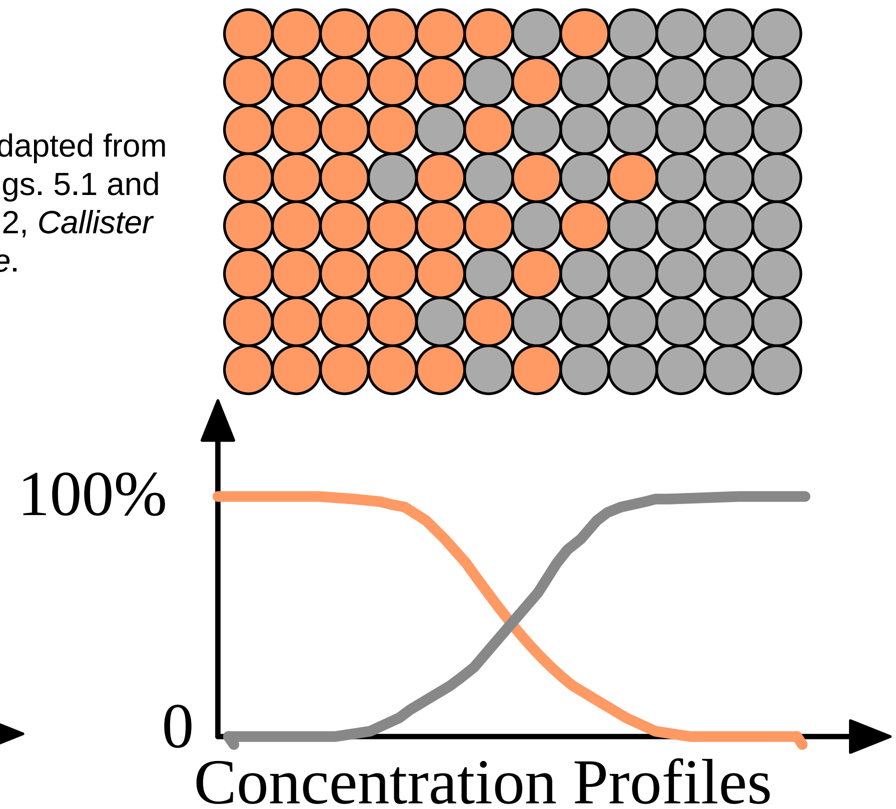
- Interdiffusion: In an alloy, atoms tend to migrate from regions of large concentration.

Initially



Adapted from Figs. 5.1 and 5.2, *Callister 6e*.

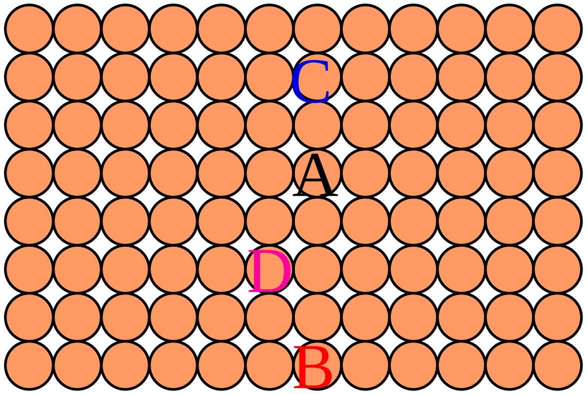
After some time



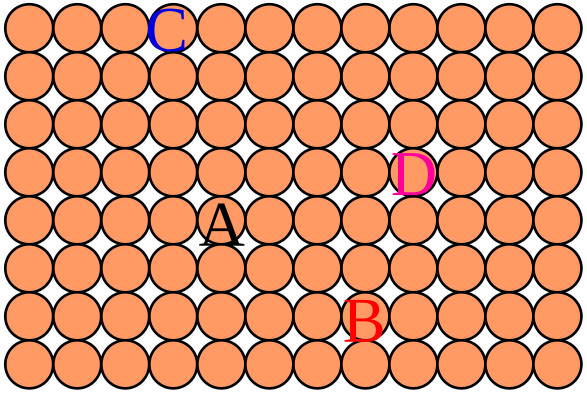
Diffusion: the phenomena (2)

- Self-diffusion: In an elemental solid, atoms also migrate.

Label some atoms



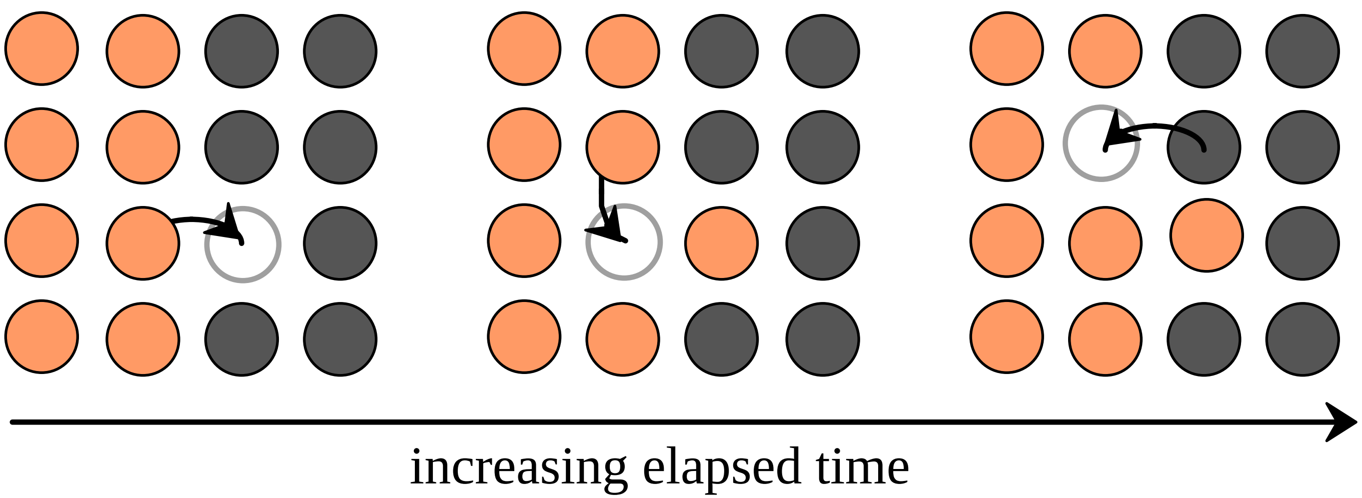
After some time



Diffusion mechanisms

Substitutional Diffusion:

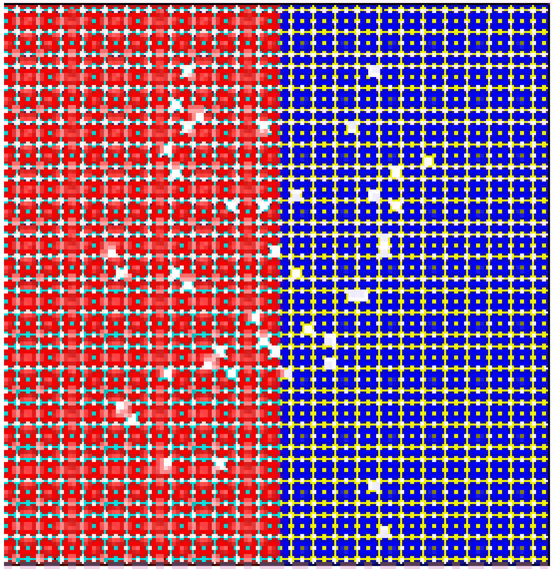
- applies to substitutional impurities
- atoms exchange with vacancies
- rate depends on:
  --number of vacancies
  --activation energy to exchange.



Diffusion simulation

- Simulation of interdiffusion across an interface:

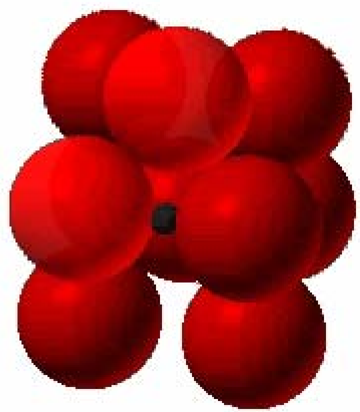
- Rate of substitutional diffusion depends on:
  --vacancy concentration
  --frequency of jumping.



(Courtesy P.M. Anderson)

Interstitial simulation

- Applies to interstitial impurities.
- More rapid than vacancy diffusion.
- Simulation:
  --shows the jumping of a smaller atom (gray) from one interstitial site to another in a BCC structure. The interstitial sites considered here are at midpoints along the unit cell edges.



(Courtesy P.M. Anderson)

Processing using diffusion (1)

- Case Hardening:
  --Diffuse carbon atoms into the host iron atoms at the surface.
  --Example of interstitial diffusion is a case hardened gear.

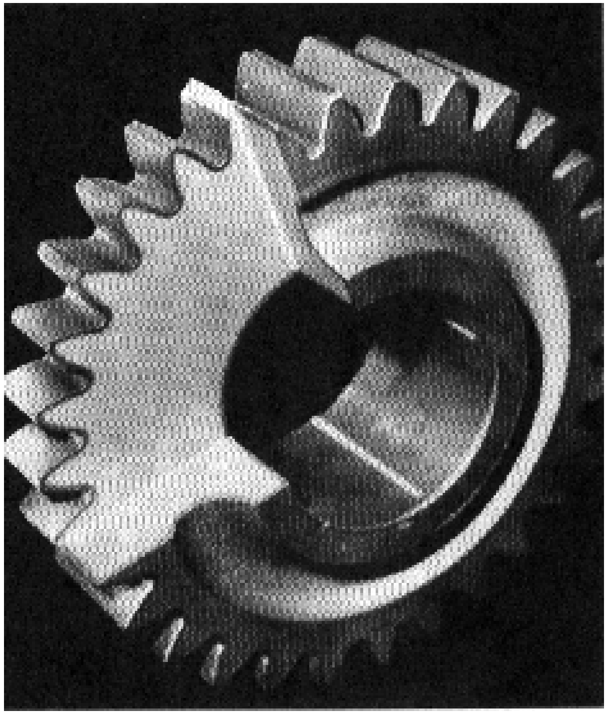
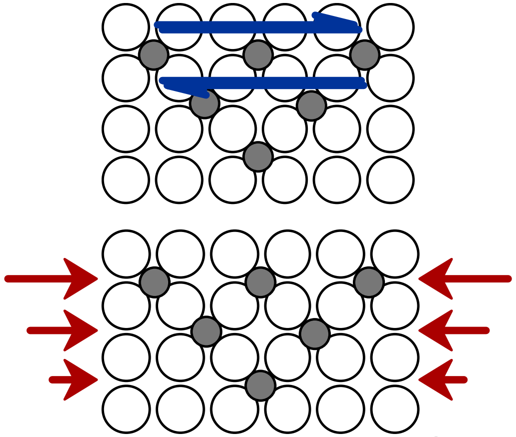


Fig. 5.0, *Callister 6e*. (Fig. 5.0 is courtesy of Surface Division, Midland-Ross.)

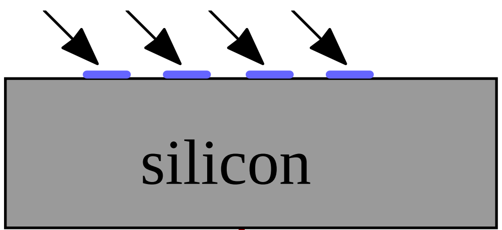
- Result: The "Case" is
  --hard to deform: C atoms "lock" planes from shearing.
  --hard to crack: C atoms put the surface in compression.



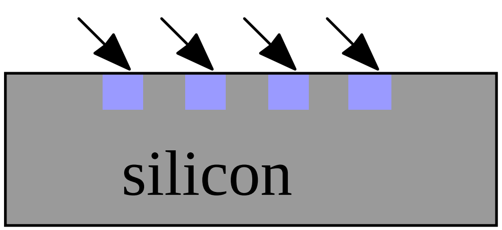
Processing using diffusion (2)

- Doping Silicon with P for n-type semiconductors:
- Process:

1. Deposit P rich
   layers on surface.



2. Heat it.
3. Result: Doped
   semiconductor
   regions.



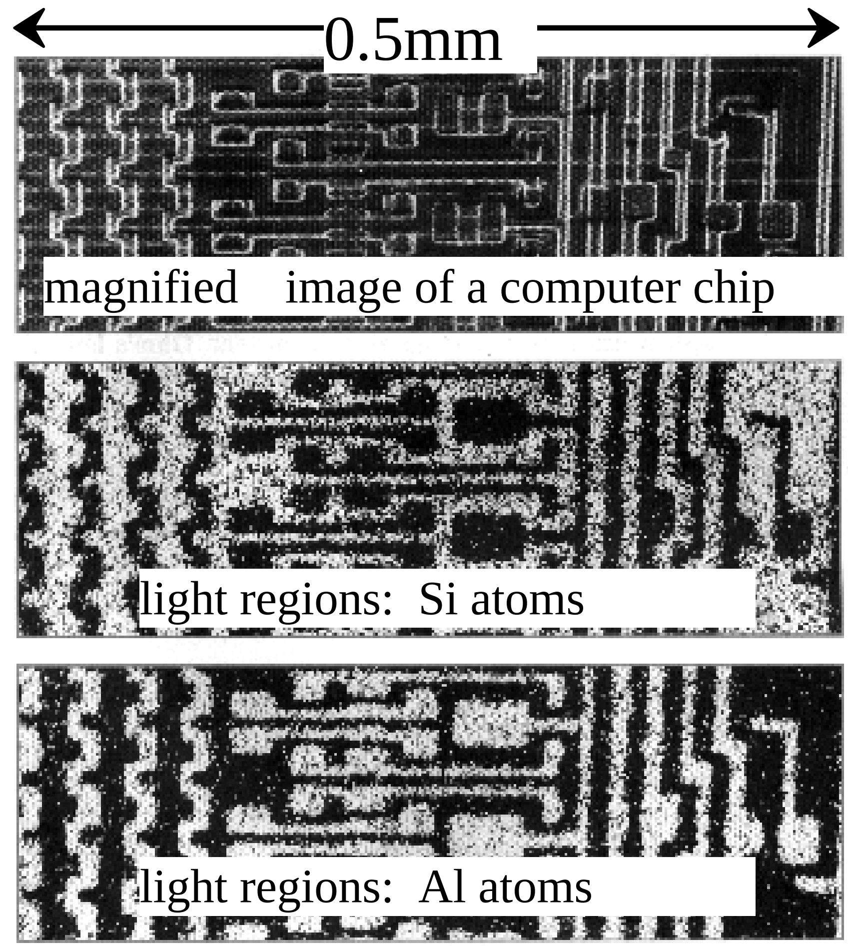


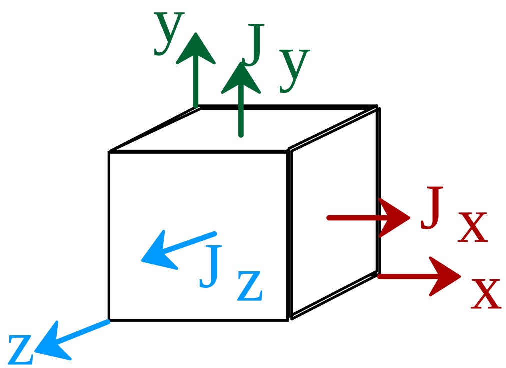
Fig. 18.0,
Callister 6e.

Modeling diffusion: flux

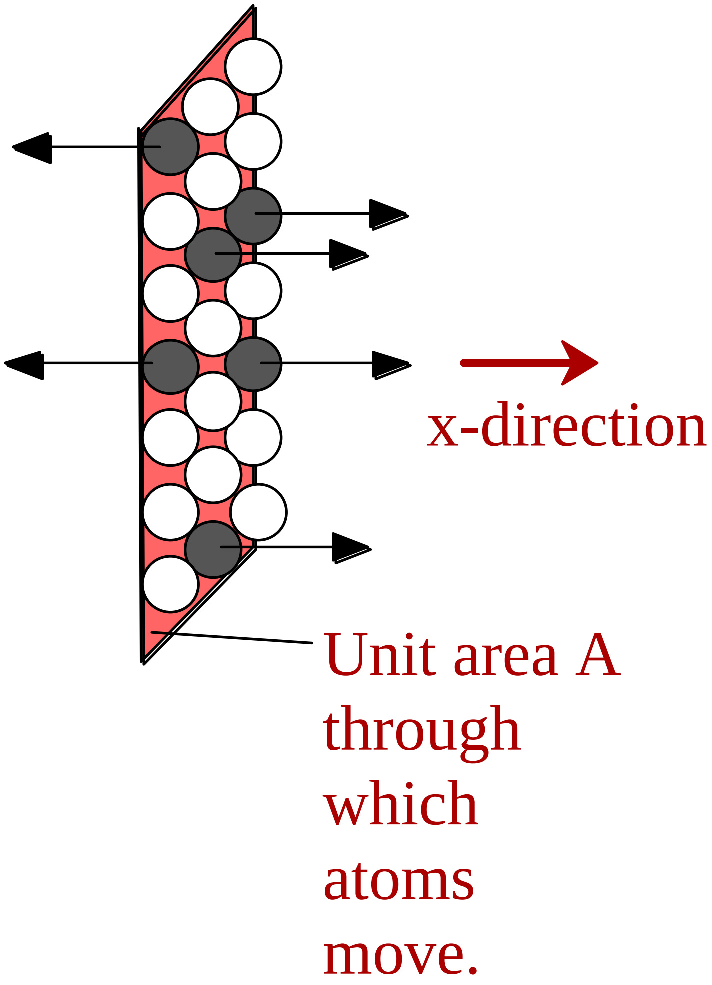
- Flux:

$$J = \frac{1}{A}\frac{dM}{dt} \Rightarrow \left[\frac{kg}{m^2 s}\right] \text{ or } \left[\frac{atoms}{m^2 s}\right]$$

- Directional Quantity

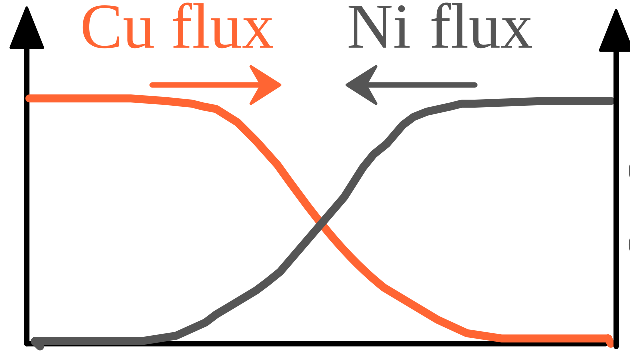


- Flux can be measured for:
  --vacancies
  --host (A) atoms
  --impurity (B) atoms



Concentration profiles & flux

- Concentration Profile, C(x): [kg/m^3]



Adapted from Fig. 5.2(c), *Callister 6e*.

- Fick's First Law:

flux in x-dir. [kg/m^2-s]

Diffusion coefficient [m^2/s]

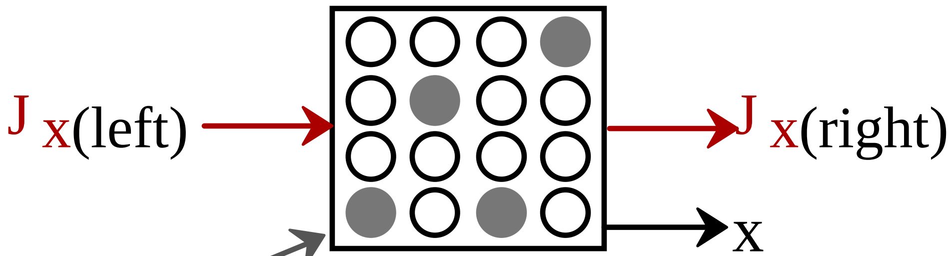
$$J_x = -D \frac{dC}{dx}$$

concentration gradient [kg/m^4]

- The steeper the concentration profile, the greater the flux!

Steady state diffusion

- Steady State: the concentration profile doesn't change with time.



Concentration, C, in the box doesn't change w/time.

Steady State:

$J_{x(\text{left})} = J_{x(\text{right})}$

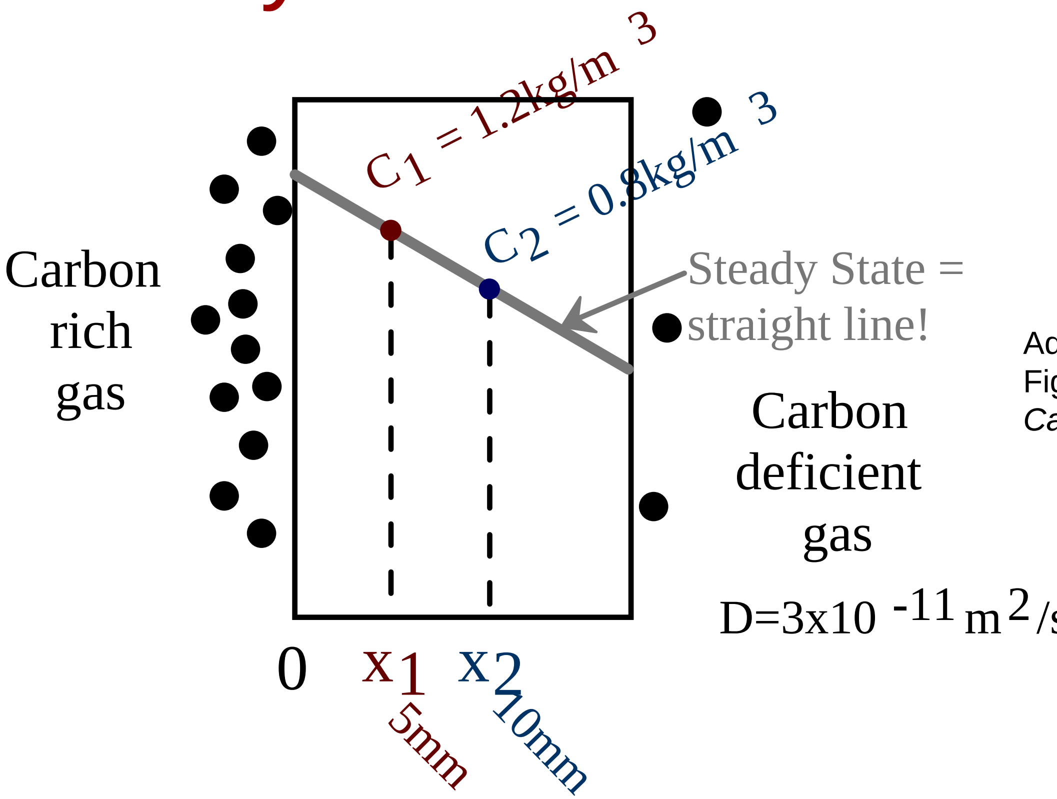
- Apply Fick's First Law: $J_x = -D\dfrac{dC}{dx}$

- If $J_x)_{\text{left}} = J_x)_{\text{right}}$, then $\left(\dfrac{dC}{dx}\right)_{\text{left}} = \left(\dfrac{dC}{dx}\right)_{\text{right}}$

- Result: the slope, dC/dx, must be constant (i.e., slope doesn't vary with position)!

Ex: Steady-state diffusion

- Steel plate at 700C with geometry shown:



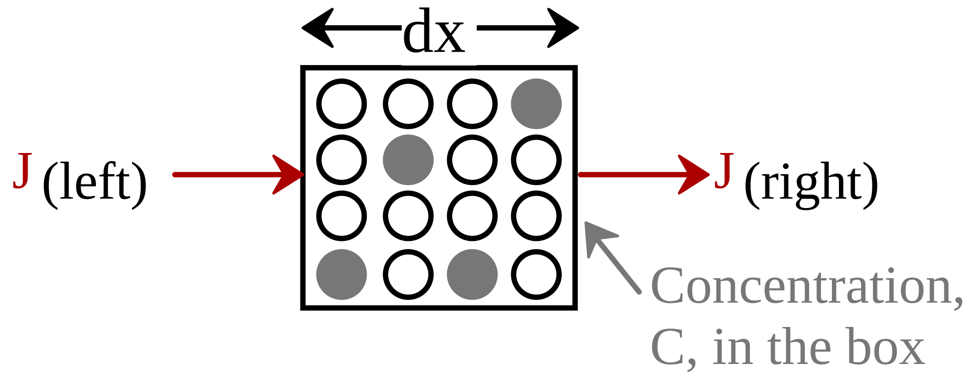
Adapted from Fig. 5.4, *Callister 6e*.

- Q: How much carbon transfers from the rich to the deficient side?

$$J = -D\frac{C_2 - C_1}{x_2 - x_1} = 2.4 \times 10^{-9} \frac{kg}{m^2 s}$$

Non steady-state diffusion

- Concentration profile, C(x), changes w/ time.



- To conserve matter:

$$\boxed{\frac{J(\text{right}) - J(\text{left})}{dx}} = -\frac{dC}{dt}$$

- Fick's First Law:

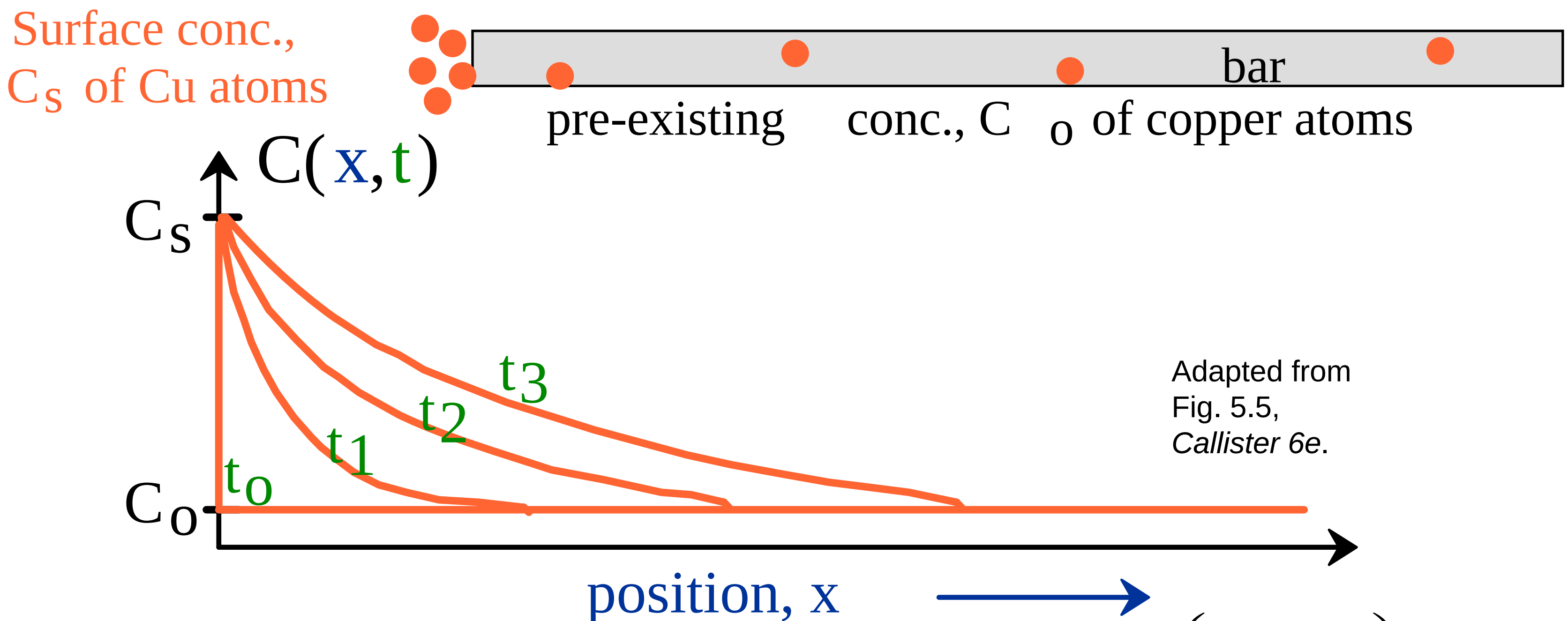
$$J = -D\frac{dC}{dx}$$ or

- Governing Eqn.:

$$\boxed{\frac{dC}{dt} = D\frac{d^2C}{dx^2}}$$

Ex: Non steady-state diffusion

- Copper diffuses into a bar of aluminum.



Adapted from Fig. 5.5, *Callister 6e*.

- General solution:

$$\frac{C(x,t)-C_o}{C_s-C_o} = 1-\mathrm{erf}\left(\frac{x}{2\sqrt{Dt}}\right)$$

"error function"

Values calibrated in Table 5.1, *Callister 6e*.

Processing question

- Copper diffuses into a bar of aluminum.
- 10 hours at 600C gives desired C(x).
- How many hours would it take to get the same C(x) if we processed at 500C?

Key point 1: $C(x,t_{500C}) = C(x,t_{600C})$.

Key point 2: Both cases have the same C_o and C_s.

$$\frac{C(x,t)-C_o}{C_s - C_o} = 1 - \mathrm{erf}\left(\frac{x}{\sqrt{2Dt}}\right) \longrightarrow \boxed{(Dt)_{500^oC} = (Dt)_{600^oC}}$$

- Result: Dt should be held constant.

- Answer:

$$t_{500} = \frac{(\overset{5.3\times10^{-13}\,m^2/s}{D}\;\overset{10hrs}{t})_{600}}{\underset{4.8\times10^{-14}\,m^2/s}{D_{500}}} = 110\ \mathrm{hr}$$

Note: values of D are provided here.

Diffusion and temperature

- Diffusivity increases with T.

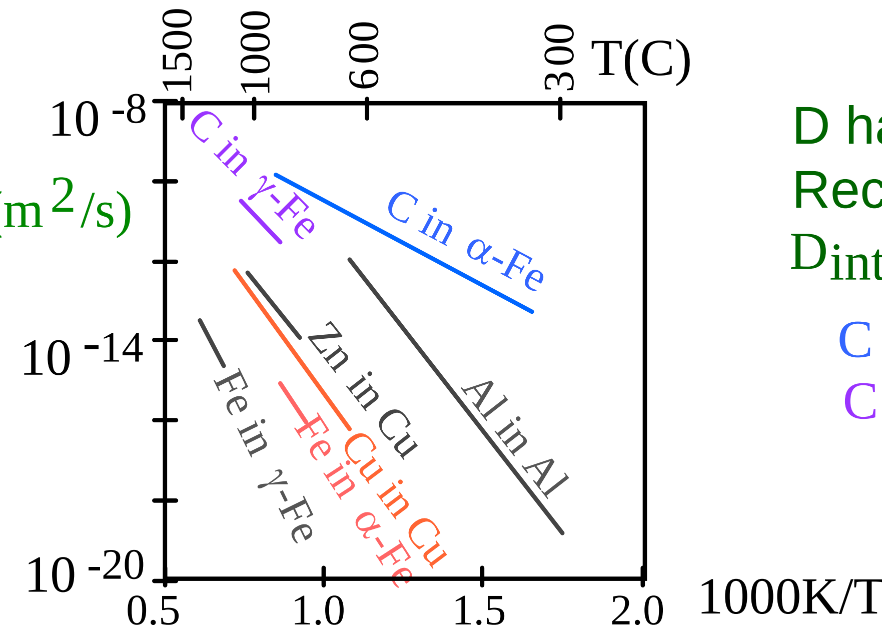
pre-exponential [m ^{2}/s]

activation energy [J/mol],[eV/mol]

diffusivity $$D = D_o \exp\left(-\frac{Q_d}{RT}\right)$$

gas constant [8.31J/mol-K]

- Experimental Data:



D has exp. dependence on T
Recall: Vacancy does also!

$D_{interstitial} >> D_{substitutional}$

C in α-Fe	Cu in Cu
C in γ-Fe	Al in Al
	Fe in α-Fe
	Fe in γ-Fe
	Zn in Cu

Summary:
structure & diffusion

Diffusion FASTER for...

- open crystal structures
- lower melting T materials
- materials w/secondary bonding
- smaller diffusing atoms
- cations
- lower density materials

Diffusion SLOWER for...

- close-packed structures
- higher melting T materials
- materials w/covalent bonding
- larger diffusing atoms
- anions
- higher density materials

ANNOUNCEMENTS

Reading: Chapter 5.1-3, and 5.5

Core Problems: Chapter 5, Problems 3 5, 7

Self-help Problems: Review Example problem 5.5